Page 1

As a below named inventor(s), I (we) hereby declare that:

My (our) residence(s), post office address(es) and citizenship(s) is (are) the same as stated before my (our)

name(s).								
I (we) believe I am (we are) an and joint inventor (if plural nan sought on the invention entitle SILICON SINGLE CRY	d: METHOD	OF MANUFACTURE	ot matte NG SII	er which is claimed and f LICON SINGLE CRYST	or which a r	nal, first patent is		
the specification of which is attached hereto unless the following box is checked:  [x] was filed on								
PCT International Application Number(If applicable).								
I (we) hereby state that I (we) including the claims, as amend	nave reviewed ded by any an	d and understand the	ne conte to above	nts of the above identifie	ed specificat	ion,		
I (we) acknowledge the duty to Federal Regulations, §1.56.	disclose info	rmation which is m	aterial to	patentability as defined	in Title 37,	Code of		
I (we) hereby claim foreign price application(s) for patent or inventor's certificate	antoi s ceminc	are listed below an	d have s	alco identified below	£	lication for		
		n Application(s):						
(Number)	(Country)		(1	Day/Month/Year)	Priority Claimed: YES NO			
2003-023148	Japan		31/01/2003		Х			
	V				<del></del>			
I (we) hereby claim the benefit application(s) listed below:	under Title 35	5, United States Co	de, §11	9(e) of any United States	provisional			
(Application Number) (Filing Date)								
I (we) hereby claim the benefit below and, insofar as the subje States application in the manna acknowledge the duty to disclo Regulation, §1.56 which becam international filing date of this a	er provided by se information ne available b	the first paragraphy which is material.	or this ap	oplication is not disclosed 35, United States Code	in the prior , § 112, I (w	United e)		
(Application Serial No.)		(Filing date)		(STATUS-patented, pending, abandoned)				
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		<u> </u>						
					·			

## DECLARATION FOR PATENT APPLICATION

I (we) hereby appoin the Patent and Patent Office:	oint the follow Trademark O	ving attorney(s) and/or agent(s)  Iffice connected therewith and t	to prosecute this apposite to act in accordance	plication and to transact all business with the instructions from Suda		
Lloyd McA Jules E. G Eugene Le Arthur Dre	oldberg, Donne,	Reg. No. 20,423; Reg. No. 24,408; Reg. No. 35,930; Reg. No. 36,612;	J. Harold Nissen, Gerald H. Kiel, Stephen M. Chin, Samir R. Patel,	Reg. No. 25,116;		
all of Reed Smith	1 LLP, 599 LEX	KINGTON AVENUE, NEW YORK, I	N.Y 10022 U.S.A.			
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4		Jules E. Goldberg, Esq. Reed Smith LLP 599 LEXINGTON AVENUE, NEW YORK, N.Y 10022 U.S.A.				
knowledge that will	on and bellet Iful false stat tle 18 of the l	are believed to be true; and fu ements and the like so made a United States Code and that su	rther that these state	are true, and that all statements ments were made with the or imprisonment, or both, under ments may jeopardize the validity of		
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Inventor's signature: Kazu hiro Harada Date: Feb. 12.04.						
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